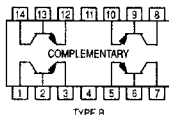


Quad Amplifier Transistors

NPN Silicon



MPQ7041
MPQ7042
MPQ7043*

*Motorola Preferred Device

MAXIMUM RATINGS

Rating	Symbol	MPQ7041	MPQ7042	MPQ7043	Unit
Collector-Emitter Voltage	V_{CEO}	150	200	250	Vdc
Collector-Base Voltage	V_{CBO}	150	200	250	Vdc
Emitter-Base Voltage	V_{EBO}	5.0			Vdc
Collector Current—Continuous	I_C	500			mAdc
		Each Die	Four Die Equal Power		
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	750 5.98	1700 13.6		mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.25 10	3.2 25.6		Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150			$^\circ\text{C}$



CASE 646-06, STYLE 1
TO-116

THERMAL CHARACTERISTICS

Characteristic		Junction to Case	Junction to Ambient	Unit
Thermal Resistance	Each Die	100	167	$^\circ\text{C}/\text{W}$
	Effective, 4 Die	39	73.5	$^\circ\text{C}/\text{W}$
Coupling Factors	Q1-Q4 or Q2-Q3	46	56	%
	Q1-Q2 or Q3-Q4	5.0	10	%

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}, I_E = 0$)	MPQ7041 MPQ7042 MPQ7043	$V_{(BR)CEO}$	150 200 250	— — —	— — —	Vdc
Collector-Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}, I_E = 0$)	MPQ7041 MPQ7042 MPQ7043	$V_{(BR)CBO}$	150 200 250	— — —	— — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100 \mu\text{Adc}, I_C = 0$)		$V_{(BR)EBO}$	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 120 \text{ Vdc}, I_E = 0$) ($V_{CB} = 150 \text{ Vdc}, I_E = 0$) ($V_{CB} = 180 \text{ Vdc}, I_E = 0$)	MPQ7041 MPQ7042 MPQ7043	I_{CBO}	— — —	— — —	100 100 100	nAdc

Preferred devices are Motorola recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Max	Unit
ON CHARACTERISTICS					
DC Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 30\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	25 40 40	45 60 80	— — —	—
Collector–Emitter Saturation Voltage ($I_C = 20\text{ mAdc}$, $I_B = 2.0\text{ mAdc}$)	$V_{CE(sat)}$	—	0.3	0.5	Vdc
Base–Emitter Saturation Voltage ($I_C = 20\text{ mAdc}$, $I_B = 2.0\text{ mAdc}$)	$V_{BE(sat)}$	—	0.7	0.9	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 10\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	50	80	—	MHz
Output Capacitance ($V_{CB} = 20\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	2.5	5.0	pF
Input Capacitance ($V_{EB} = 3.0\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	—	40	50	pF

DC CHARACTERISTICS

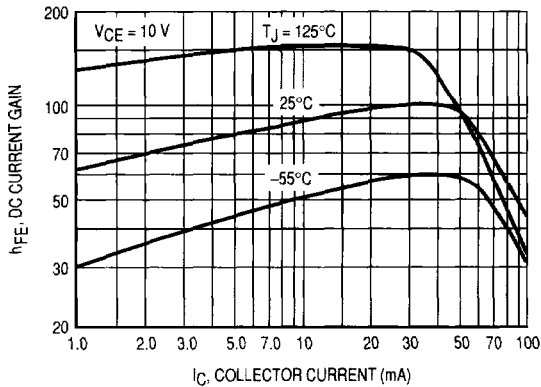


Figure 1. DC Current Gain

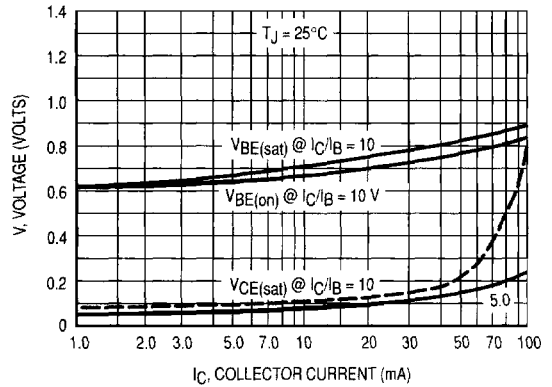


Figure 2. "ON" Voltages

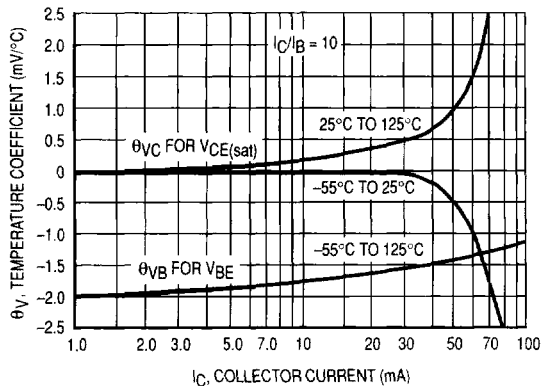


Figure 3. Temperature Coefficients